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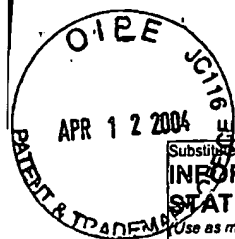
Substitution for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/052952
	Filing Date	January 17, 2002
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2874
	Examiner Name	Rahll, Jerry
Sheet 1 of 8		Attorney Docket No: 1303.034US1

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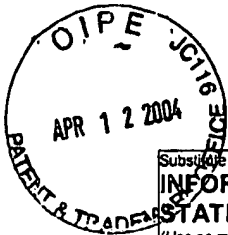
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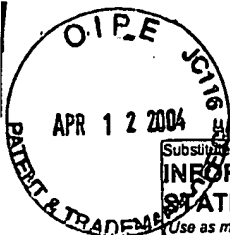
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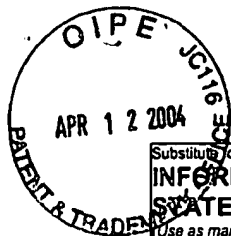
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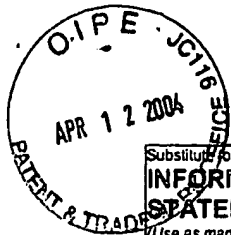
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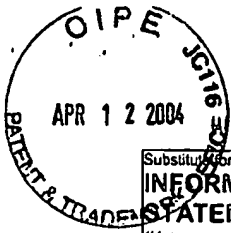
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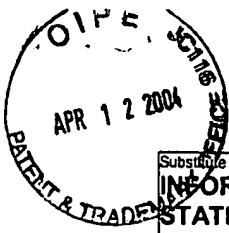
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JTR		VERDONCKT-VANDEBROEK,, SOPHIE , et al., "SiGe-Channel Heterojunction p-MOSFET's", <u>IEEE Transactions on Electron Devices</u> , 41(1), (January 1994), 90-101	
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DATE CONSIDERED

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/052952
Filing Date	January 17, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2874
Examiner Name	Rahll, Jerry

Sheet 8 of 8

Attorney Docket No: 1303.034US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Jm3		YIN, HAIZHOU, "High Ge-Content Relaxed Si1-xGex Layers by Relaxation on Complaint Substrate with Controlled Oxidation", <u>Electronic Materials Conference, Santa Barbara, June 2002, (June 2002),8</u>	
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